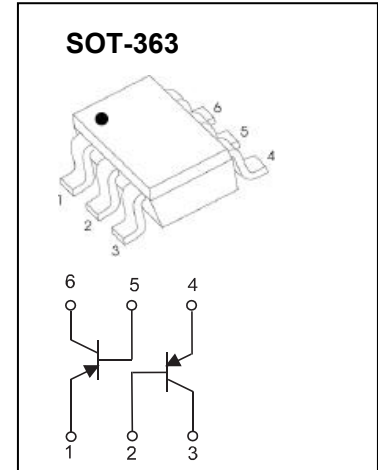


Plastic-Encapsulate Transistors

TRANSISTOR (PNP)

FEATURES

- Complementary to MMDT9014DW
- MARKING: TGM6



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-45	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _c	Collector Current	-100	mA
P _c	Collector Power Dissipation	200	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	625	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _c = -100μA, I _E = 0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c = -0.1mA, I _B = 0	-45			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _c = 0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -50 V, I _E = 0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _c = 0			-0.1	μA
DC current gain	h _{FE}	V _{CE} = -5V, I _c = -1mA	300		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c = -100mA, I _B = -10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c = -100mA, I _B = -10mA			-1	V
Base-emitter saturation voltage	V _{BE}	V _{CE} = -5V, I _B = -2mA	-0.6		-0.75	V
Transition frequency	f _t	V _{CE} = -5V, I _c = -10mA f = 30MHz	150			MHz



CHINA BASE
INTERNATIONAL

SOT-363

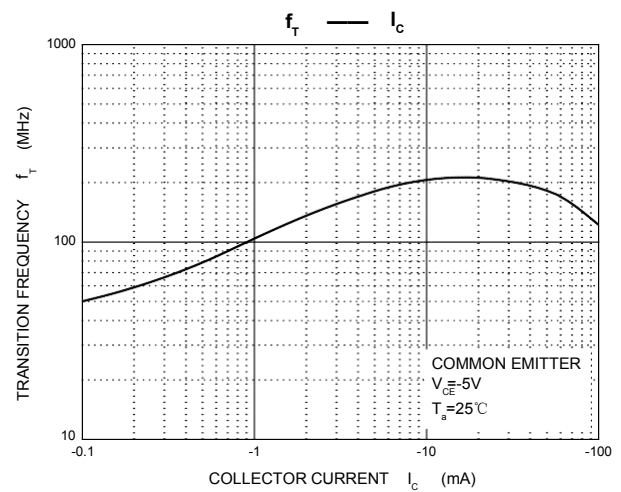
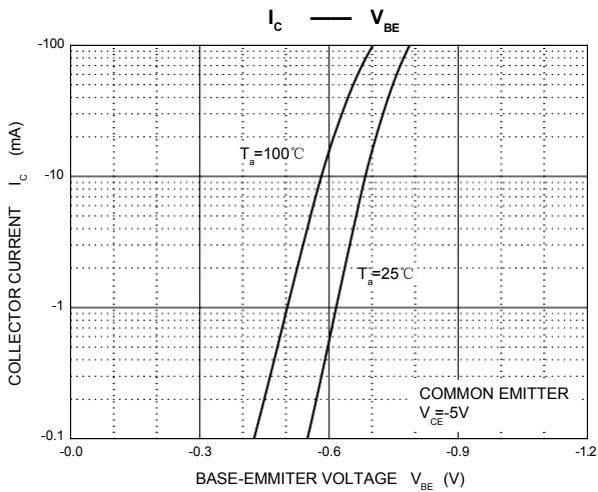
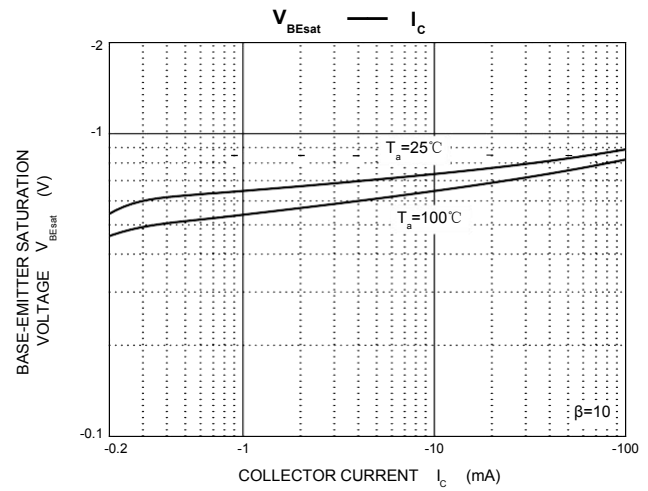
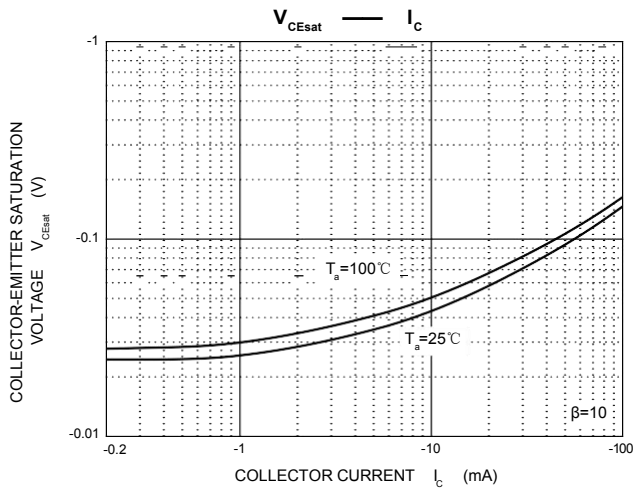
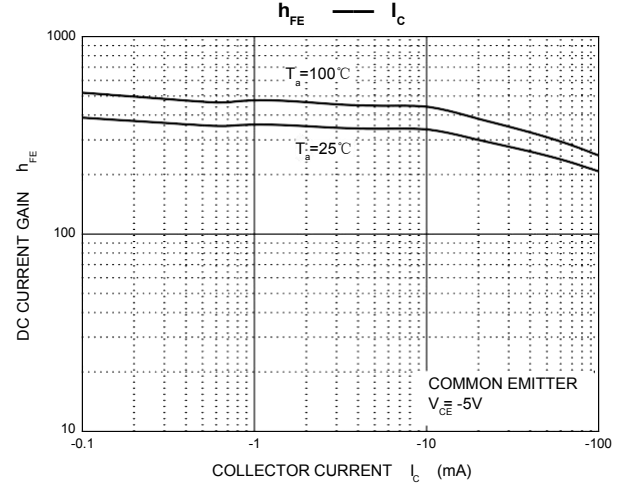
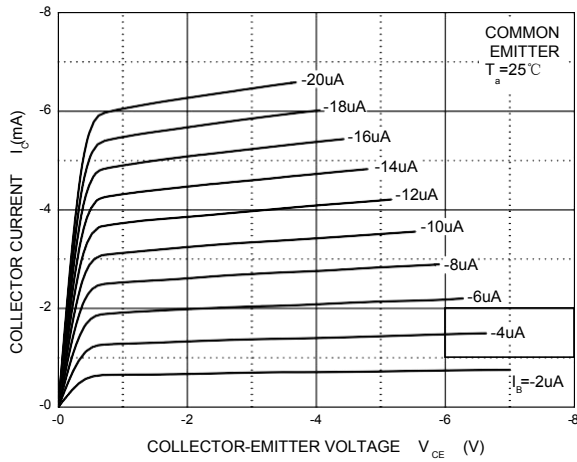
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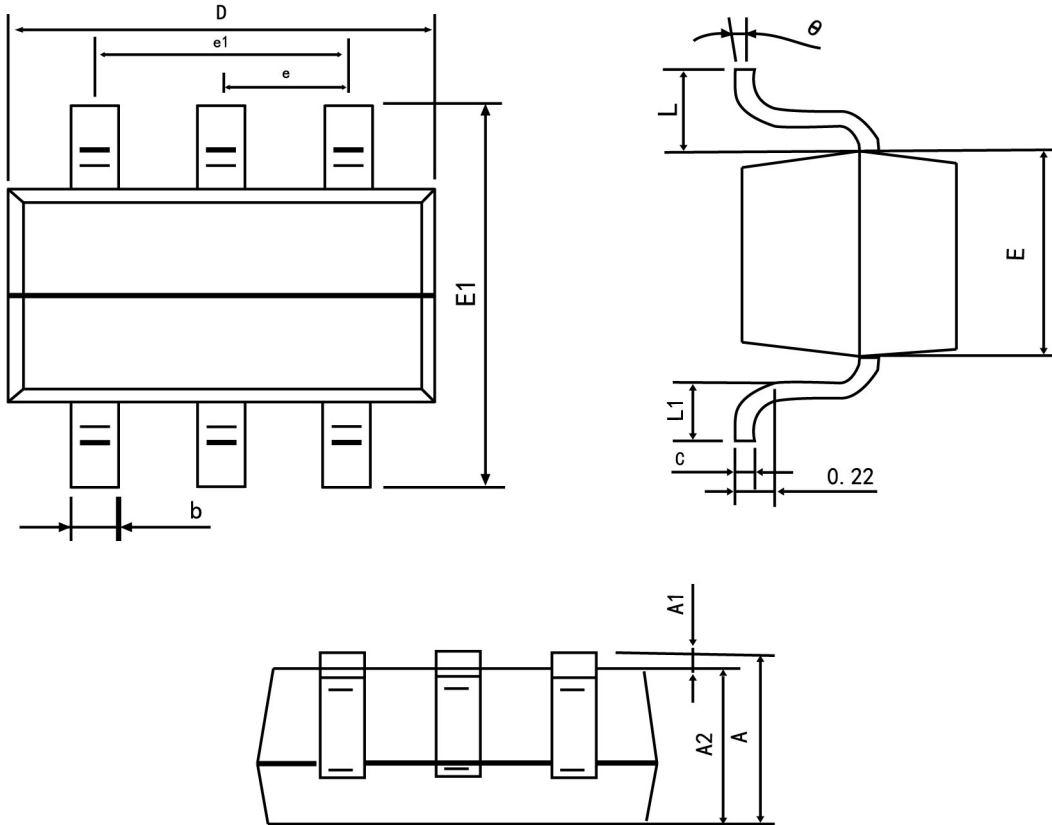
Typical Characteristics

Static Characteristic





SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°